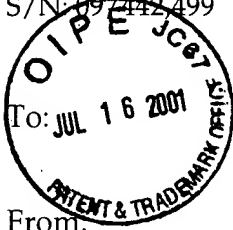


Docket: CS 99 - 065  
S/N: 09/442,499



Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Front:

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*Handwritten initials and date: Hg/B, 2/19/01, Msa*

Subject:

Serial No. 09/442,499	Filed: 11/18/99
Inventor: Ho	
Title: Plasma Etch Method For Forming Plasma Etched Silicon Layer	
Group Art Unit: 1763	Examiner: Goudreau, B.
Attorney Docket: CS 99 - 065	

### RESPONSE TO PATENT OFFICE ACTION

Dear Sir:

In response to the office action dated 05/11/01, please consider the following remarks:

### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patent and Trademarks, Washington, D.C. 20231, on

July 11, 2001.

Signature/Date

*George O. Saile 7/11/01*  
*George O. Saile, Reg#19,572*

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01 FC:103 144.00 CH  
02 FC:102 240.00 CH